

A New Class of Magnetoresistance Oscillations: Interaction of a Two-Dimensional Electron Gas with Leaky Interface Phonons

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We report on a new class of magnetoresistance oscillations observed in a high-mobility two-dimensional electron gas (2DEG) in GaAs-AlGaAs heterostructures. Being periodic in $1/B$, these oscillations appear in a weak magnetic field ($B < 0.3$ T) and only in a narrow temperature range ($3 \text{ K} < T < 7 \text{ K}$). Remarkably, these oscillations can be understood in terms of magneto-phonon resonance originating from the interaction of the 2DEG with thermally excited leaky interface-acoustic phonon modes. The existence of such modes at the GaAs-AlGaAs interface is demonstrated theoretically and their velocities are calculated. It is shown that the electron-phonon scattering matrix element exhibits a peak for those phonons carrying wave vector $q = 2k_F$, where k_F is the Fermi wave vector of the 2DEG.

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There are several different classes of transverse magnetoresistance oscillations that exist in both two- and three-dimensional homogeneous electron gases. The most common of these are Shubnikov-de Haas (SdH) oscillations, which arise from a magnetic field (B)-induced modulation of the density of states at the Fermi level E_F . They become more pronounced with decreasing temperature. The magneto-phonon resonance (MPR) [1,2] is another source of oscillations, owing to the absorption of bulk longitudinal optical phonons. These resonances appear under the condition $\omega_{LO} = l\omega_c$, where ω_{LO} and $\omega_c = eB/mc$ are the optical phonon and cyclotron frequencies respectively, l is an integer, and m is the effective mass of the carriers. These oscillations are only seen at relatively high temperatures (100-200 K). Both SdH effect and MPR are periodic in $1/B$. However, MPR is independent of the electron density n_e , while the period of SdH depends on the density as $n_e^{-2/D}$, where D is the space dimensionality.

In this Letter, we report on a new class of magnetoresistance oscillations [3,4], unrelated to either of the above origins, which we discovered in a high-mobility two-dimensional electron gas (2DEG) in GaAs-Al_{0.3}Ga_{0.7}As heterostructures. These novel oscillations are periodic in $1/B$, appearing at weak magnetic fields ($B < 0.3$ T) and *only* in a narrow temperature range ($3 \text{ K} < T < 7 \text{ K}$). Moreover, we observe these oscillations only in a high-mobility ($\mu \geq 2 \times 10^6 \text{ cm}^2/\text{Vs}$) 2DEG. Remarkably, the effect can be understood in terms of a magneto-acoustic phonon resonance (MAPR) originating from the interaction of the 2DEG with *thermally excited leaky interface-acoustic phonon* (LIP) modes. Our theoretical calculations demonstrate the existence of LIP modes on the GaAs-AlGaAs interface. Using the bulk moduli of the host lattices, we calculate the velocity u

of these modes, which is found to be in good agreement with experiment. Analysis of the electron-phonon scattering matrix element shows that, in the presence of a weak B field, the 2DEG interacts selectively with the interface phonons carrying wave vector $q = 2k_F$, where k_F is the Fermi wave vector of the 2DEG at zero B field. The condition for resonant absorption or emission of the LIP by the 2DEG is then given by

$$2k_F u = l\omega_c, \quad l = 1, 2, 3, \dots \quad (1)$$

We claim that Eq. (1) determines the values of magnetic field for the maxima in these new magneto-oscillations. It shows that the oscillations are periodic in $1/B$ and their period is $\Delta(1/B) = e/(2k_F u m c)$, as observed experimentally. It is important, that the novel oscillations arise solely due to the two-dimensionality of the electron layer, and the selection rule $q = 2k_F$ assumes that q is a *lateral* wave vector of the phonon. Note that the bulk phonons can not account for the MAPR, since their frequency depends on q_z , and the above selection rule becomes irrelevant.

Our samples are lithographically defined (width 100 μm) Hall bars of high-mobility GaAs-Al_{0.3}Ga_{0.7}As wafers grown by MBE. While similar oscillations have been observed in a variety of samples, here, we present the data mainly from one specimen with an electron density $n_e = 2.17 \times 10^{11} \text{ cm}^{-2}$ and a mobility $\mu \approx 3 \times 10^6 \text{ cm}^2/\text{Vs}$, achieved by a brief illumination from a red light-emitting diode at $T = 4 \text{ K}$. The density-dependent data were obtained from a similar specimen having a CrNi front gate. The distance between the electrons and the Si δ -doping layer is $d_s \approx 700 \text{ \AA}$. The experiments were performed in a variable-temperature liquid ^4He cryostat equipped with a superconducting magnet, employing a standard low-frequency (3 to 7 Hz) lock-in technique to measure the resistance.

In Fig. 1(a) we show the low-field magnetoresistivity $\rho_{xx}(B)$ measured at $T = 4$ K. In addition to the damped SdH effect commonly seen in a 2DEG at this temperature, the trace reveals a new oscillations that appear only at $B < 0.3$ T. The arrows next to the trace indicate the first three (indexed as $l = 1, 2, 3$) $\rho_{xx}(B_l)$ maxima in this oscillatory structure.

Such a structure may, in principle, arise from the SdH effect of electrons occupying the upper subband of the potential well. However, since the inter-subband separation in GaAs-AlGaAs heterostructures is typically > 200 K, and E_F in our sample is about 80 K, we do not expect significant population of the second subband at low temperatures. Furthermore, the corresponding Landau level (LL) splitting in GaAs ($\hbar\omega_c \approx 2$ K at 0.1 T) is too small for SdH to be observed at 4 K. Finally, the disappearance of the oscillations at lower temperature [Fig. 2(a)] is inconsistent with SdH. We conclude that SdH cannot account for the observed oscillatory structure.

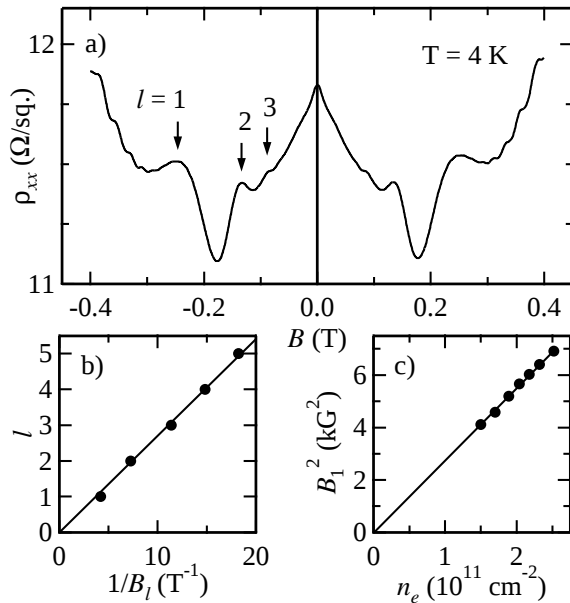


FIG. 1. a) Magnetoresistivity at $T = 4$ K showing a new oscillations beyond SdH effect at $B < 0.3$ T; maxima for $l = 1, 2, 3$ are marked by arrows; b) l vs. $1/B_l$ (circles) and fit (line) using Eq. (1) reveals $u = 3.0$ km/s; c) B_1^2 vs. n_e .

Rather, the observed oscillations can be analyzed consistently in terms of MAPR [Eq. (1)]. Analysis of the second derivative $d^2\rho_{xx}(B)/dB^2$ of the trace in Fig. 1(a) gives a plot of l vs. $1/B$, shown in Fig. 1(b). It demonstrates the periodicity of the oscillations in reciprocal magnetic field in accordance with Eq. (1). A linear fit to the data (solid line) generates the phonon velocity $u = 3.0$ km/s. In Fig. 1(c) we plot the square of the magnetic field position of the primary maximum, *i.e.*, $B_{l=1}$ as a function of n_e measured in the gated sample. Since $k_F = \sqrt{2\pi n_e}$, the observed linear dependence implies that $B_1 \propto k_F$ as prescribed by Eq. (1). A linear fit (solid line) leads to the the same value of $u = 3.0$ km/s.

To further support the MAPR scenario, we present the $\rho_{xx}(B)$ traces at several temperatures ranging from 1.9 K to 9.1 K in Fig. 2(a). While the SdH effect gradually diminishes as T increases, the MAPR oscillations are best developed at $T \sim 4 - 6$ K, and are strongly damped at both higher and lower temperatures. We also note [Fig. 2(b)] that the zero-field resistivity $\rho_{xx}(0)$ grows linearly with T implying that acoustic-phonon scattering dominates the electron mobility in this temperature range [5,6]. The characteristic temperature for an acoustic phonon can be estimated from the linear dispersion with $q = 2k_F$, *i.e.*, $k_B T = \hbar u(2k_F)$, which for our system is found to be 5.1 K using the experimental value $u = 3.0$ km/s. At the temperatures much lower than 5 K such phonon modes are strongly suppressed by Plank's function, therefore the oscillation amplitudes diminish. At high temperatures the smearing of the LL's becomes important and the oscillations disappear as well.

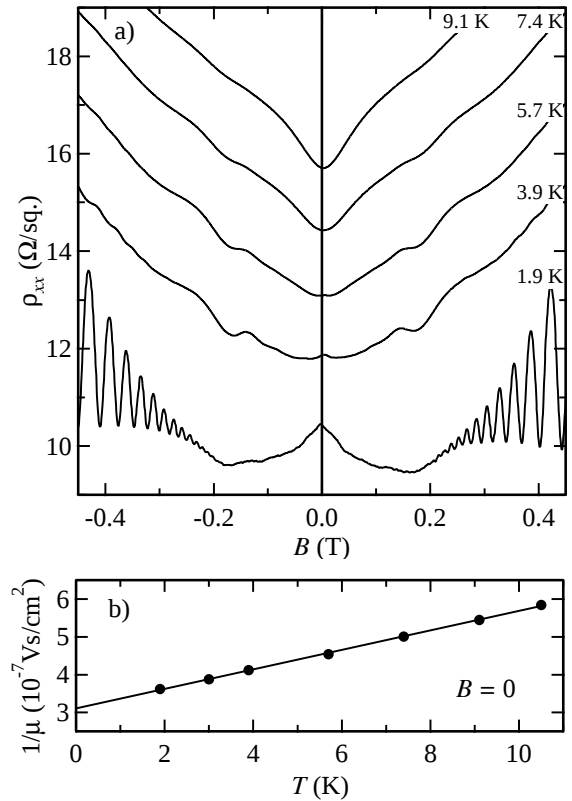


FIG. 2. a) Magnetoresistivity at different T showing that oscillations are best developed around 4 K and are strongly suppressed at higher and lower temperatures; b) a linear dependence is shown for inverse zero-field mobility vs. temperature.

We devote the rest of the paper to a discussion of our theoretical model based on the scattering of the 2DEG by leaky-interface phonons. The possibility of waves propagating along an interface was demonstrated by Stoneley [7]. He derived the dispersion relation for the velocity of a propagating wave, assuming that both media are

isotropic. It has been found that for some values of parameters a localized mode at the interface, the so called Stoneley wave (STW), can exist. The frequency of the STW is a linear function of the wave vector: $\omega = u_{stw}q$, and its velocity u_{stw} must lie between the velocities of a surface wave u_{sur} and a transverse wave u_t in the denser medium, *i.e.*, $u_{sur} < u_{stw} < u_t$. The STW's exist only under rather restrictive conditions on the bulk elastic properties of the two media. One can see that the interface we consider, namely GaAs-AlGaAs cut perpendicular to the [001] direction, does not possess STW's for any reasonable values of the bulk parameters in anisotropic approximation.

However, the Stoneley dispersion relation admits other solutions, which are the LIP modes. These modes are attenuated as they propagate along the interface. Since the theory does not take into account any energy dissipation, such attenuation is only due to the radiation of energy away from the interface. As a consequence the values of frequency and velocity become complex: $u = \omega/q = u_R - iu_I$ with $u_I \ll u_R$. So far only optical leaky waves have been detected at the interfaces [8], while acoustic leaky phonons have been found at a free surface [9]. The amplitude of such waves grows exponentially with increasing distance in the direction perpendicular to the interface. Nevertheless, we can still consider them as regular phonons. A nice physical explanation of this fact can be found in Ref. [10]. The anisotropic case has been considered numerically [11] for Cu based materials. Another method for calculation of interface phonons is based on surface Green function matching [12]. A good review of the theory of both surface and interface phonons can be found in Ref. [13].

We have performed calculations of LIP modes for the GaAs-Al_{0.3}Ga_{0.7} interface [14]. Using elastic moduli of the bulk materials [15] we have derived the anisotropic dispersion relation for LIP with the velocity along two directions of high symmetry, namely [110] and [100]. The slowest LIP mode has the complex velocity $u = 3.1(3.2) + i0.08(0.09)$ km/s in [110]([100]) direction which is in good agreement with our experimental value of 3.0 km/s derived using Eq. (1). The study of group velocities of these waves shows that the energy flows towards the bulk AlGaAs, forming a glancing angle of $\sim 10^\circ$ with the interface. The next upper LIP branch (with the real part of velocity 4.7 km/s and stronger attenuation) is suppressed at the temperature of our experiments and is ignored in the rest of our analysis. Since $u_R([110]) \approx u_R([100])$, we also suggest that the behavior of the slowest LIP is isotropic.

To calculate the transverse conductivity due to the scattering of the 2DEG on LIP's, we employ a 2D analogue of the formula, first derived by Titeica [16]:

$$\sigma_{xx} = \frac{4\pi e^2}{Am^2 kT \omega_c^2} \sum_{n,n'} \sum_{k_y, k'_y} \sum_{q_x, q_y} |I_{nn'}(q\lambda)|^2 q_y^2 |C(q)|^2 \times N_l f_n (1 - f_{n'}) \delta_{k_y - k'_y + q_y} \delta(\omega_c(n' - n) - qu). \quad (2)$$

Here A is the area, $N_l = (\exp(\hbar\omega/kT) - 1)^{-1}$, $f_n = (\exp((E_n - \mu)/kT) + 1)^{-1}$, $\lambda = \sqrt{\hbar c/eB}$ is the magnetic length, and $|C(q)|^2 \equiv v(q)/A$ is the square modulus of the 2DEG-LIP interaction, which has a power law dependence on q . This formula can be interpreted in the following way. A 2D electron in a magnetic field has a wave function which is a product of a plane wave in the y direction and an oscillatory wave function, centered at the position $x_0 = -\hbar k_y/eB$: $\Psi = \exp(ik_y y) \phi_n(x - x_0)$, where n is the LL index. In the absence of scattering the electric current may flow only in the y -direction, providing the Hall effect. A transverse conductivity appears because an electron transfers wave vector $q_y = k'_y - k_y$ to a scatterer. This is equivalent to a jump in the x -direction at a distance $\Delta x_0 = \hbar q_y/eB$. In Eq. (2) this physics is applied to electron scattering by the interface phonons.

The mechanism of the 2DEG-LIP interaction, which may be either deformation potential or piezoelectric interaction, is not particularly important for the explanation of the novel magneto-oscillations. We also include in $C(q)$ the part of the matrix element connected with the wave function perpendicular to the plane that can be taken in the Fang-Howard approximation [17]. Note, that the amplitude of the LIP wave increases towards AlGaAs, where the electron wave function vanishes [14].

If the interface phonon has no attenuation, the square of matrix element $I_{nn'}$ is given by [17]

$$|I_{n,n+l}(b)|^2 = \left| \int_{-\infty}^{+\infty} e^{iq_x x} \phi_n(x - x_0) \phi_{n+l}(x - x'_0) dx \right|^2 = \frac{n!}{(n+l)!} \left(\frac{b^2}{2} \right)^l e^{-\frac{b^2}{2}} \left[L_n^l \left(\frac{b^2}{2} \right) \right]^2, \quad (3)$$

where $b = q\lambda$ and $L_n^l(x)$ is the generalized Laguerre polynomial.

Substituting summation over wave vectors by integration in Eq. (2) one obtains

$$\sigma_{xx} = \frac{e^2}{2\pi\hbar} \frac{1}{mkT\omega_c} \sum_{n,l} N_l f_n (1 - f_{n+l}) \times \int_0^\infty dq q^3 v(q) |I_{n,n+l}(q\lambda)|^2 \delta(\omega_c l - qu). \quad (4)$$

Taking into account the imaginary part of the LIP frequency, $\omega = q(u_R + iu_I)$, we can substitute for the δ -function in Eq. (4) a Gaussian distribution with appropriate dispersion $\sigma = qu_I$. Since the dispersion is small we can set $q = \omega_c l/u_R$ everywhere except for the strongly oscillating function $|I_{nl}(q\lambda)|^2$. Then after averaging we obtain for the transverse conductivity

$$\sigma_{xx} = \frac{e^2/2\pi\hbar}{mu\omega_c kT} \sum_{l,n} v \left(\frac{\omega_c l}{u} \right) F_{nl} N_l f_n (1 - f_{n+l}), \quad (5)$$

where the function F_{nl} can be expressed as a series of Hermit polynomials of imaginary argument:

$$F_{nl} = \frac{(\omega_c l / u)^3}{\sqrt{1 + \alpha^{-1}}} \exp\left(-\frac{\alpha}{1 + \alpha} \frac{\hbar \omega_c l^2}{2mu^2}\right) \sum_{k,j}^n \frac{n!(-1)^l}{(n+l)!k!j!} \left(\begin{matrix} n+l \\ n-k \end{matrix} \right) \left(\begin{matrix} n+l \\ n-j \end{matrix} \right) \frac{H_{2(k+j+l)}\left(il\sqrt{\frac{\hbar\omega_c}{2mu^2}} \frac{\alpha}{\sqrt{1+\alpha}}\right)}{[2\sqrt{1+\alpha}]^{2(k+l+j)}}, \quad (6)$$

with $\alpha = (u/\sigma\lambda)^2$. Hereafter, we assume that u is the real part of the LIP velocity. In Fig. 3 we plot F_{nl} for $n = 17$ and $l = 1$ as a function of B for LIP with $\sigma = \omega_c u_I / u_R$ (solid line) and in the limit $\sigma = 0$ (dashed line).

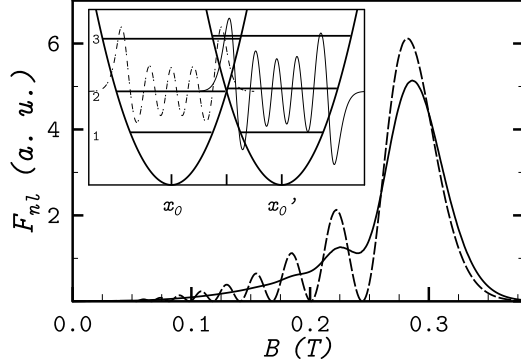


FIG. 3. $F_{17,1}(B)$ in the limit $\sigma = 0$ (dashed line) and for LIP (solid line). The inset schematically shows the origin of the strongest peak in the function $F_{nl}(B)$.

As we can see, once attenuation is introduced, there remains only one strong peak that corresponds to Eq. (1) at $l = 1$ implying that $2k_F = 2\sqrt{2n}/\lambda$. This means that only phonons with wave vector $q = 2\sqrt{2n}/\lambda$ effectively interact with electrons under the condition $n \gg 1$. In fact, due to the Fermi distribution in Eq. (5) only the values of $n \approx E_F/\hbar\omega_c$ are important. Then, indeed, $2\sqrt{2n}/\lambda = 2\sqrt{2\pi n_e} = 2k_F$, and we arrive at Eq. (1) for $l = 1$. The same conclusion holds for any $l \ll n$.

This is an important result of our work. It can be interpreted from the following semi-classical consideration (see the inset in Fig. 3). Let us consider $n \sim n' \gg 1$. Since the square of the matrix element in Eq. (3) depends on q only, we can put $q_x = 0$. Then the integrand in (3) is an overlap of two oscillatory wave functions shifted with respect to each other. In the vicinity of the turning point the wave function always has a maximum since the momentum is small and the particle spends the most part of its time there. There are three possibilities. Cases 1 and 3 in the inset show situations when turning points are apart from each other, and case 2 occurs when the turning points coincide in space. Obviously, in case 2 the overlap integral has a maximum. This occurs when $m\omega_c^2(\Delta x_0)^2/8 = n\hbar\omega_c$, which is equivalent to the above condition $q\lambda \approx 2\sqrt{2n}$. Note that other maxima in Fig. 3 can be smeared very easily because their widths are proportional to $n^{-1/2}$, while the first maximum near the turning point can be approximated by Airy function and its width is independent of n . Thus, the maxima in

$F_{nl}(B)$ for different l 's give rise to oscillations in $\rho_{xx}(B)$.

In conclusion, we have discovered a new class of magneto-oscillations in a high-mobility 2DEG and interpreted it as the magneto-phonon resonance with leaky acoustic interface phonons. Owing to the dispersion of the acoustic modes, it had earlier been believed that only optical modes, not the acoustic modes, may be used for phonon spectroscopy in a 2DEG. Our work may open up a new method for phonon spectroscopy in 2DEG, including resonance of ballistic interface phonons with correlated electronic states in GaAs-AlGaAs heterostructures.

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